

MBRS540T3

Preferred Device

Surface Mount Schottky Power Rectifier

The MBRS540T3 employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Small Compact Surface Mountable Package with J-Bend Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Guard-Ring for Stress Protection
- Pb-Free Package is Available

Mechanical Characteristics

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 217 mg (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Polarity: Notch in Plastic Body Indicates Cathode Lead
- ESD Rating: Machine Model, C (> 400 V)
Human Body Model, 3B (> 8000 V)
- Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
Average Rectified Forward Current (At Rated V_R , $T_C = 105^\circ\text{C}$)	$I_{F(AV)}$	5	A
Peak Repetitive Forward Current (At Rated V_R , Square Wave, 20 KHz, $T_C = 80^\circ\text{C}$)	I_{FRM}	10	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	190	A
Storage Temperature Range	T_{stg}	-65 to +150	°C
Operating Junction Temperature (Note 1)	T_J	-65 to +150	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.



ON Semiconductor®

SCHOTTKY BARRIER RECTIFIER 5.0 AMPERES, 40 VOLTS



SMC
CASE 403
PLASTIC

MARKING DIAGRAM



B540 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBRS540T3	SMC	2500/Tape & Reel
MBRS540T3G	SMC (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MBRS540T3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead (Note 2)	$R_{\theta JL}$	12	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	111	

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 3)	($i_F = 5.0 \text{ A}$, $T_C = 25^{\circ}C$)	V_F	0.50	V
Maximum Instantaneous Reverse Current (Note 3)	(Rated dc Voltage, $T_C = 25^{\circ}C$)	i_R	0.3	mA
	(Rated dc Voltage, $T_C = 100^{\circ}C$)		15	

2. Rating applies when surface mounted on the minimum pad size recommended.

3. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

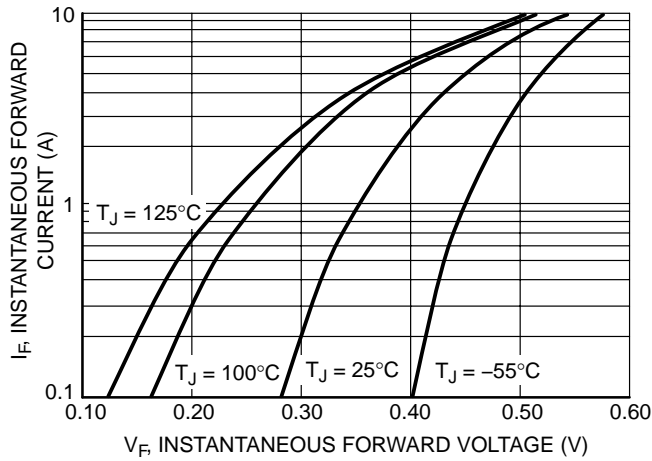


Figure 1. Typical Forward Voltage

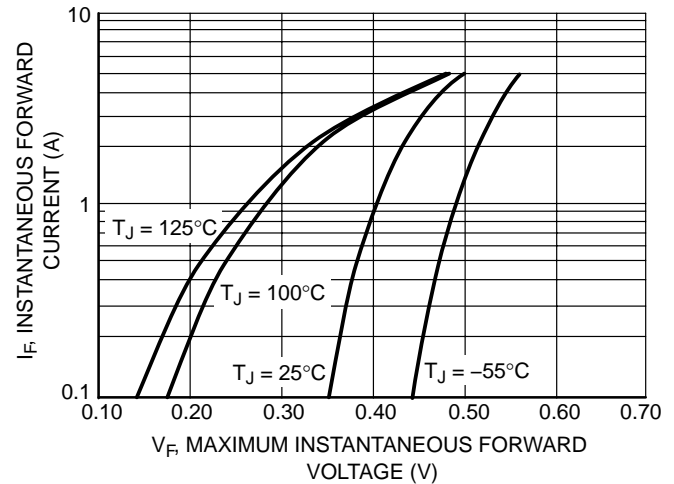


Figure 2. Maximum Forward Voltage

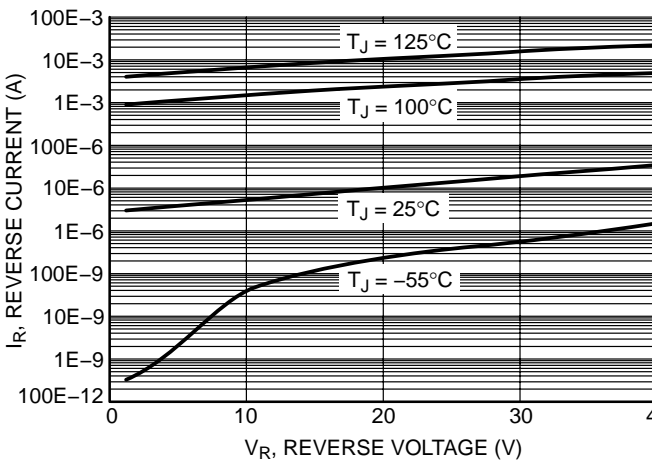


Figure 3. Typical Reverse Current

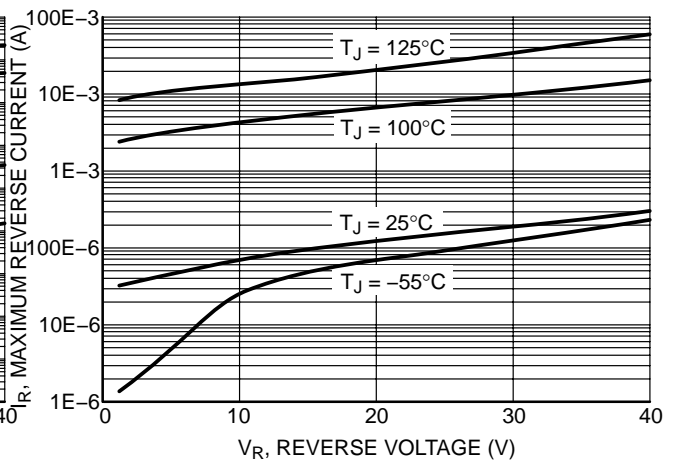
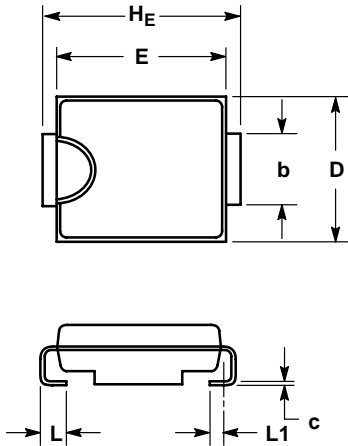


Figure 4. Maximum Reverse Current

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PACKAGE DIMENSIONS

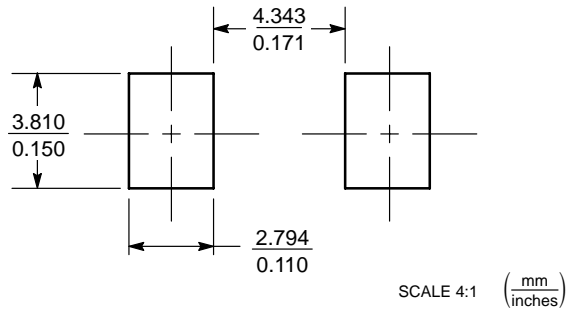
SMC
CASE 403-03
ISSUE E



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.
 4. 403-01 THRU -02 OBSOLETE, NEW STANDARD 403-03.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.90	2.13	2.41	0.075	0.084	0.095
A1	0.05	0.10	0.15	0.002	0.004	0.006
b	2.92	3.00	3.07	0.115	0.118	0.121
c	0.15	0.23	0.30	0.006	0.009	0.012
D	5.59	5.84	6.10	0.220	0.230	0.240
E	6.60	6.86	7.11	0.260	0.270	0.280
HE	7.75	7.94	8.13	0.305	0.313	0.320
L	0.76	1.02	1.27	0.030	0.040	0.050
L1	0.51 REF			0.020 REF		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.